

SHEET 1 of 2

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INFORMATION DISCLOSURE  
CITATION

PTO-1449

Atty. Docket No.	Serial No.
NTI-029	10/005,615
Applicant	
CHANG, Fang-Cheng	
Filing Date	Group
11/7/2001	2825

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
WJ	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
	6,154,563	11/28/2000	Tsudaka	382	144	12/17/1998
	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
	6,338,922 B1	1/15/2002	Liebmann, et al.	430	5	5/8/2000
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SHEET 2 of 2

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	NTI-029	10/005,615
	<b>Applicant</b>	CHANG, Fang-Cheng
	<b>Filing Date</b>	<b>Group</b>
	11/7/2001	2825

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SHEET 1 of 6

<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		Atty. Docket No.	Serial No.			
		NTI-029	10/005,615-9717			
		Applicant				
		CHANG, Fang-Cheng				
		Filing Date	Group 2825			
		11/7/2001	<del>100</del>			
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
WD	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
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	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
	5,815,685	9/29/1998	Kamion	395	500	9/15/1995
	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
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	6,249,597 BI	6/19/2001	Tsudaka	382	144	12/17/1998

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<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		Atty. Docket No. NTI-029	Serial No. 10/005,615-9717
		Applicant CHANG, Fang-Cheng	Group <u>2825</u> <u>1100</u>
		Filing Date 11/7/2001	

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**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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WS	JP 3-80525	4/5/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
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	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	GB 2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/14638 A1	3/25/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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		<b>Applicant</b> CHANG, Fang-Cheng	
		<b>Filing Date</b> 11/7/2001	<b>Group</b> 2825

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EXAMINER: John Morris

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<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>	
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Atty. Docket No. **NTI-029** Serial No. **10/005,615-9717**  
 Applicant **CHANG, Fang-Cheng**  
 Filing Date **11/7/2001** Group **2825**  
**2825**

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<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		<b>Atty. Docket No.</b> NTI-029 <b>Applicant</b> CHANG, Fang-Cheng <b>Filing Date</b> 11/7/2001	<b>Serial No.</b> 10/005,615-9717 <b>Group</b> 2825 <del>5555</del>
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		Applicant CHANG, Fang-Cheng	Group <u>2825</u> <u>1444</u>
		Filing Date 11/7/2001	
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